

N-channel TrenchMOS logic level FET 19 March 2014

Product data sheet

### 1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources

## 3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

## 4. Quick reference data

Table 1. Q	uick reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	-	55	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>sp</sub> = 25 °C; <u>Fig. 3</u> ; <u>Fig. 2</u>	-	-	7	А
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; <u>Fig. 1</u>	-	-	8	W
Static chara	cteristics					
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C	-	62	73	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C	-	-	89	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 13;</u> <u>Fig. 14</u>	-	68	80	mΩ
Avalanche r	uggedness	·				
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 6 A; $V_{sup} \le 55$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	36	mJ

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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	4	D
2	D	drain		
3	S	source		G-UFT 4
4	D	drain	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	mbb076 S

### 6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
BUK9880-55A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			
BUK9880-55A/CU	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

# 7. Marking

Table 4.   Marking codes	
Type number	Marking code
BUK9880-55A	988055A
BUK9880-55A/CU	988055

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	55	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ	-	55	V
V <sub>GS</sub>	gate-source voltage		-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; <u>Fig. 1</u>	-	8	W
I <sub>D</sub>	drain current	T <sub>sp</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>	-	4	А
		T <sub>sp</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 3; Fig. 2</u>	-	7	А
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; pulsed; $t_p \le 10 \ \mu s$ ; Fig. 3	-	30	А

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Symbol	Parameter	Conditions		Min	Мах	Unit
T <sub>stg</sub>	storage temperature			-55	150	°C
Tj	junction temperature			-55	150	°C
V <sub>GSM</sub>	peak gate-source voltage	pulsed; $t_p \le 50 \ \mu s$		-15	15	V
Source-drain	diode					
I <sub>S</sub>	source current	T <sub>sp</sub> = 25 °C		-	7	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{sp} = 25 \ ^\circ C$		-	30	А
Avalanche ru	iggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 6 \text{ A}; V_{sup} \le 55 \text{ V}; \text{ R}_{GS} = 50 \Omega;$ $V_{GS} = 5 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ unclamped}$		-	36	mJ
E <sub>DS(AL)R</sub>	repetitive drain-source avalanche energy	<u>Fig. 4</u>	[1][2][3][	<u>4]</u>	-	J

[1] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 150 °C.

[3] Repetitive avalanche rating limited by an average junction temperature of 145 °C.

[4] Refer to application note AN10273 for further information.

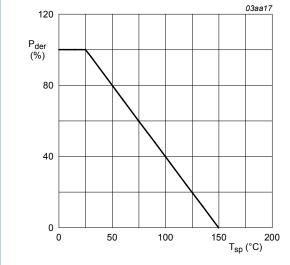


Fig. 1. Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

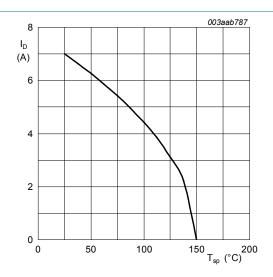


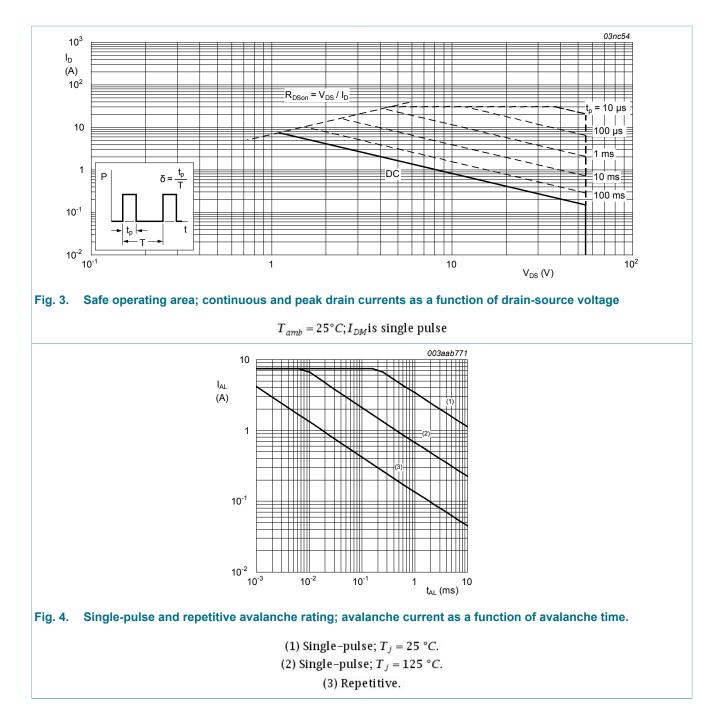
Fig. 2. Continuous drain current as a function of solder point temperature

 $V_{GS} \ge 5V$ 

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### 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	15	K/W

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t<sub>p</sub> |

10

t<sub>p</sub> (s)

10<sup>2</sup>

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	<u>Fig. 5</u>	-	120	-	K/W
					03nc55	
10 <sup>2</sup> Z <sub>th(j-sp)</sub> (K/W)						
10 δ	= 0.5					
-0	2					
-0 1 =0						
0.	02		P		$\delta = \frac{t_p}{T}$	
10 <sup>-1</sup>						

10<sup>-2</sup>

10<sup>-1</sup>

1

#### Fig. 5. Transient thermal impedance from junction to solder point as a function of pulse duration

10<sup>-3</sup>

10<sup>-4</sup>

### **10. Characteristics**

10<sup>-2</sup>

Single Shot

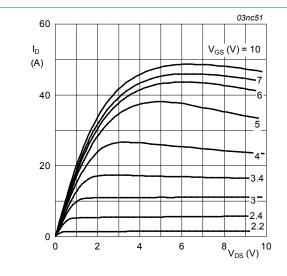
10<sup>-5</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics	· · · · · ·	1			
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	50	-	-	V
	breakdown voltage	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	55	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 12; Fig. 8	1	1.5	2	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 150 °C; Fig. 12; Fig. 8	0.6	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 12; Fig. 8	-	-	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 55 V; $V_{GS}$ = 0 V; $T_j$ = 150 °C	-	-	500	μA
		$V_{DS}$ = 55 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.05	10	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub> drain-source on-stat resistance	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 150 °C; Fig. 13; Fig. 14	-	-	147	mΩ
		$V_{GS}$ = 10 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C	-	62	73	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C	-	-	89	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ;	-	68	80	mΩ
		<u>Fig. 14</u>				
Dynamic cl	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	-	11	-	nC	
Q <sub>GS</sub>	gate-source charge	Fig. 11	-	1.6	-	nC
Q <sub>GD</sub>	gate-drain charge	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 44 V; V <sub>GS</sub> = 5 V; Fig. 15	-	4.6	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	438	584	pF
C <sub>oss</sub>	output capacitance		-	87	104	pF
C <sub>rss</sub>	reverse transfer capacitance		-	62	85	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 5 V;	-	8	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 10 Ω; T <sub>j</sub> = 25 °C	-	118	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	20	-	ns
t <sub>f</sub>	fall time		-	32	-	ns
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 15 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 17</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = -100 A/μs;	-	33	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS}$ = -10 V; $V_{DS}$ = 30 V; $T_j$ = 25 °C	-	60	-	nC





 $T_j=25^\circ C$ 

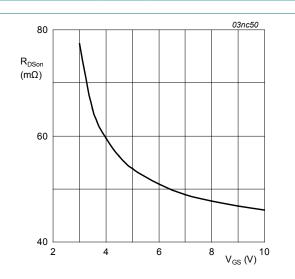
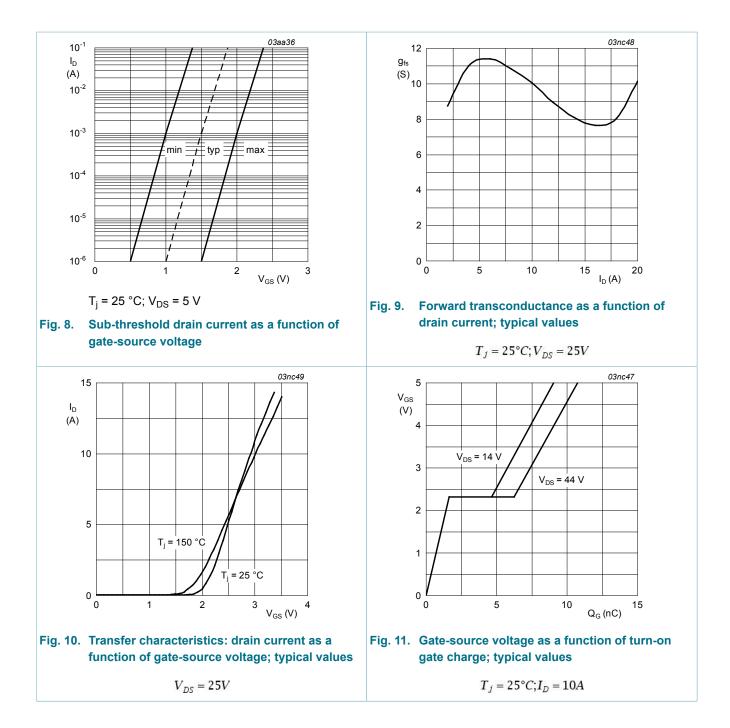


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j=25^\circ C; I_D=10A$ 

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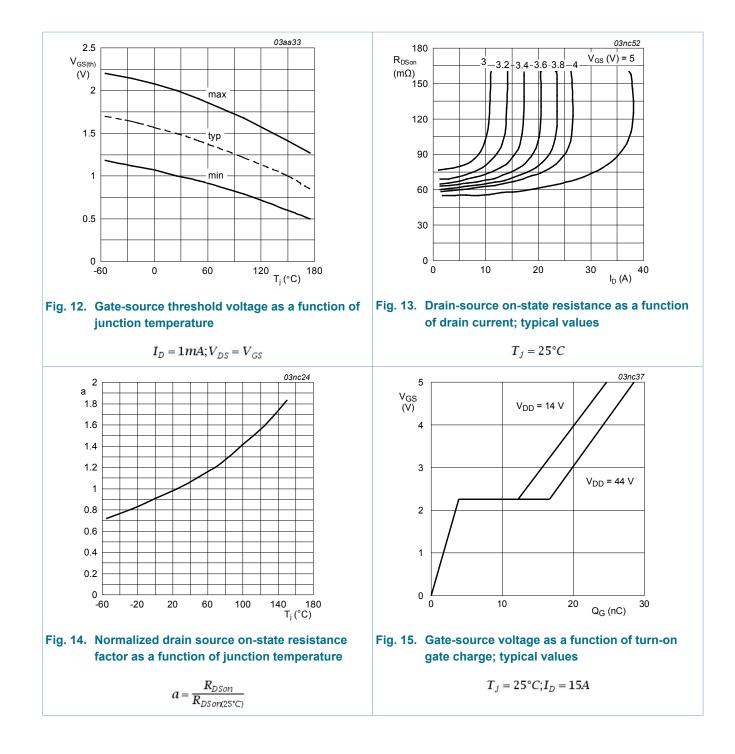
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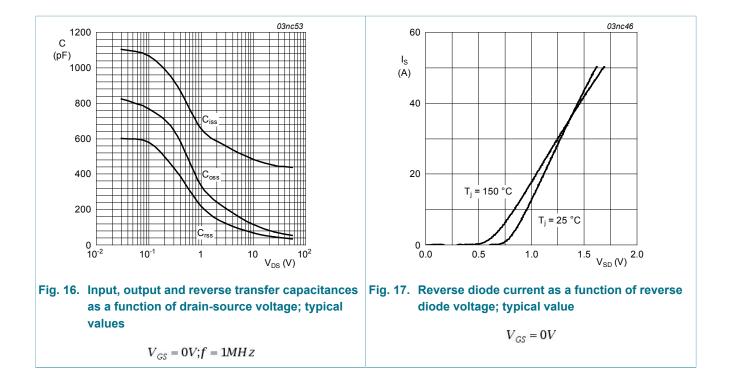
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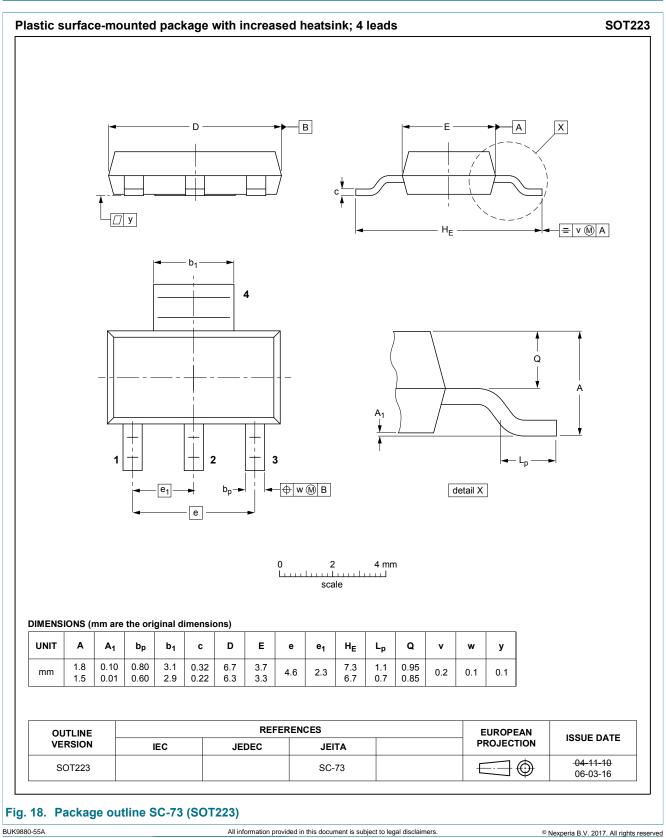
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### **11. Package outline**



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### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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